

Product Summary

BV _{DSS}	R _{DS(on)} max	I _D T _A = +25°C
001/	50mΩ @ V _{GS} = 10V	6.7A
60V	$70m\Omega @ V_{GS} = 4.5V$	5.7A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC converters
- Power management functions
- Backlighting

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/

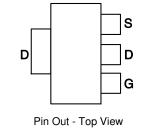
Mechanical Data

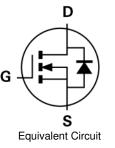
- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.112 grams (Approximate)



SOT223 (Type DN)







Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A25GTA	ZXMN6A25	7	12	1,000

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

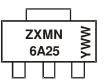
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

SOT223 (Type DN)



 $\begin{array}{l} ZXMN6A25 = \mbox{Product Type Marking Code} \\ YWW = \mbox{Date Code Marking} \\ Y \ or \ \overline{Y} = \mbox{Last Digit of Year (ex: 2 = 2022)} \\ WW \ or \ \overline{WW} = \ Week \ Code \ (01{\sim}53) \end{array}$



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristi	Symbol	Value 60	Units V		
Drain-Source Voltage	V _{DSS}				
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ (Note 6) $T_A = +70^{\circ}C$ (Note 6) $T_A = +25^{\circ}C$ (Note 5)	ID	6.7 5.4 4.8	А
Maximum Body Diode Forward Current (Note 6)			ls	5.7	А
Pulsed Drain Current (Note 7)			I _{DM}	28.5	А
Pulsed Source Current (Note 7)			I _{SM}	28.5	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation Linear Derating Factor	T _A = +25°C (Note 5)	PD	2 16	W mW/°C
Total Power Dissipation Linear Derating Factor	T _A = +25°C (Note 6)	PD	3.9 31	W mW/°C
Steady state (Note 5) Steady state (Note 6)		R _{0JA}	62.5 32	°C/W °C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)						-	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	—	1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	Igss		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)			•	•	•		
Gate Threshold Voltage	V _{GS(th)}	1.0	_	_	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 8)	Б	_	_	50	mΩ	$V_{GS} = 10V, I_D = 3.6A$	
Static Drain-Source On-Resistance (Note 8)	R _{DS(on)}	_	—	70	11122	$V_{GS} = 4.5V, I_D = 3.0A$	
Diode Forward Voltage (Note 8)	V _{SD}	_	0.85	0.95	V	$V_{GS} = 0V, I_S = 5.5A$	
Forward Transconductance (Note 8 & 10)	g fs		10.2	_	S	$V_{DS} = 15V, I_D = 4.5A$	
DYNAMIC CHARACTERISTICS (Note 10)			•	•	•		
Input Capacitance	Ciss	_	1,063	—	pF	$V_{DS} = 30V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	Coss	_	104	_			
Reverse Transfer Capacitance	C _{rss}	_	64	_			
Total Gate Charge (V _{GS} = 5.0V)	Qg	_	11	_		$V_{DS} = 30V, I_D = 1.4A,$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	20.4	_	nC		
Gate-Source Charge	Qgs	_	4.1	_	nc		
Gate-Drain Charge	Q _{gd}		5.1	_			
Turn-On Delay Time	t _{D(on)}		3.8	_		$\label{eq:VGS} \begin{split} V_{GS} &= 10V, V_{DD} = 30V, R_G = 6.0\Omega, \\ I_{D} &= 1.0A \end{split}$	
Turn-On Rise Time	tr		4.0		nS		
Turn-Off Delay Time	t _{D(off)}		26.2				
Turn-Off Fall Time	t _f		10.6		1		
Body Diode Reverse Recovery Time	t _{rr}		22		nS		
Body Diode Reverse Recovery Charge	Q _{rr}		21.4		nC	I _F = 2.2A, dI/dt = 100A/µs	

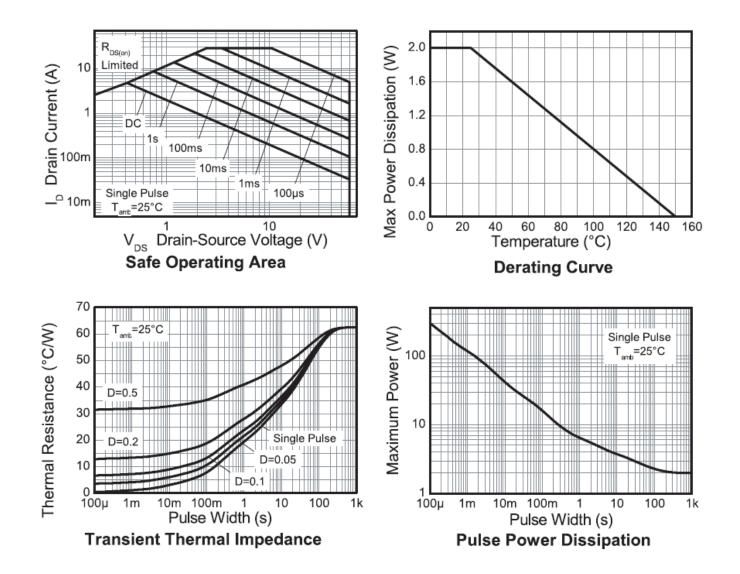
5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions 6. For a device surface mounted on FR4 PCB measured at t \leq 10 secs. Notes:

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Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

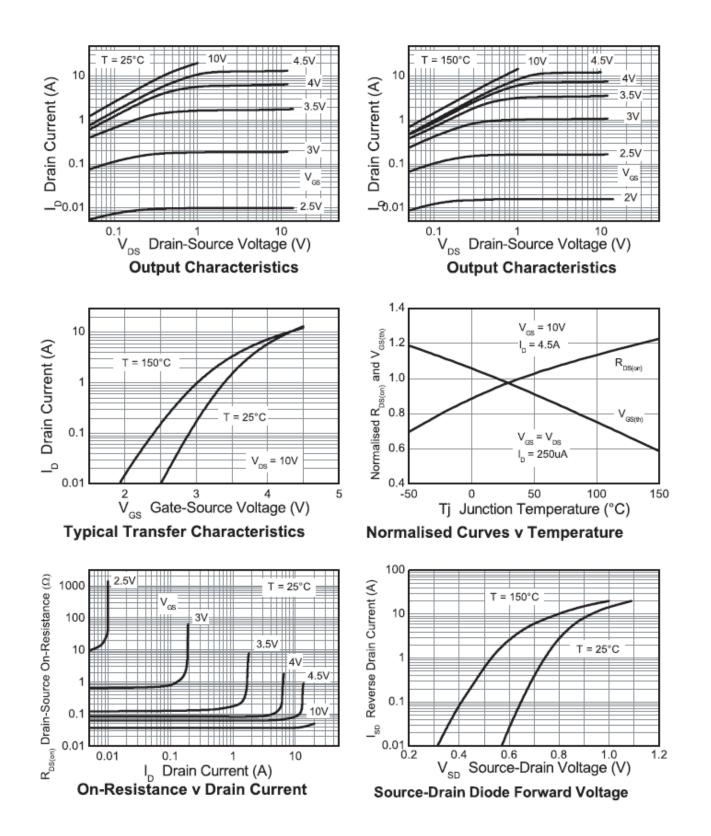


Typical Characteristics



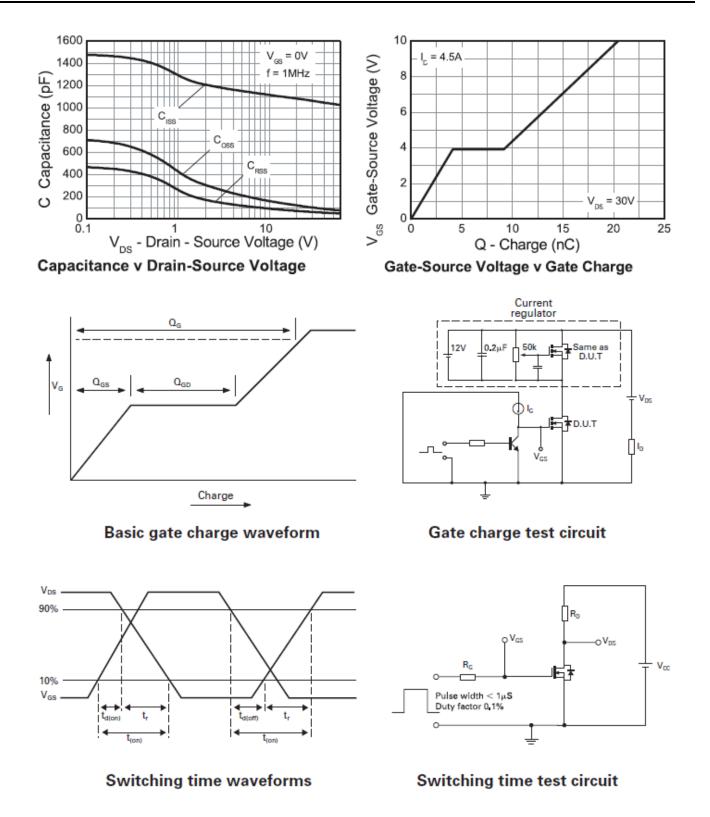


Typical Characteristics (continued)





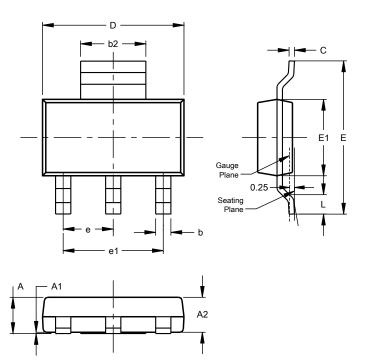
Typical Characteristics (continued)





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



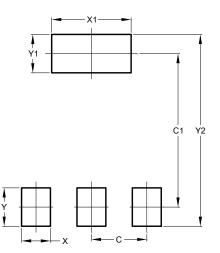
SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
Е	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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